

**In the Claims:**

1. (original) A method of forming an electronic device comprising:  
providing an inner semiconductor substrate;  
forming a buried conductive layer on the outer surface of the inner substrate;  
forming a semiconductive bonding layer on an outer surface of the buried conductive layer; and  
bonding an outer substrate to the outer surface of the bonding layer, the outer substrate comprising a buried insulator layer having a surface bonded to the outer surface of the bonding layer, the outer substrate further comprising a semiconductor device layer disposed outwardly from the buried insulator layer.
2. (original) The method of Claim 1, wherein the conductive layer comprises tungsten.
3. (original) The method of Claim 1, wherein the conductive layer comprises titanium nitride.
4. (original) The method of Claim 1, wherein the bonding layer comprises deposited amorphous silicon.
5. (original) The method of Claim 1, wherein the buried insulator layer comprises silicon dioxide.
6. (original) The method of Claim 1, wherein the device layer comprises single crystalline silicon.